

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 8 A, 650 V, D1, T0-220F-2L

FFSPF0865A

Description

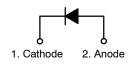
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 49 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

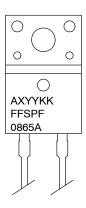


Schottky Diode



TO-220 FP / TO-220F-2FS CASE 221AS

MARKING DIAGRAM



A = Assembly Plant Code

XYY = Data Code (Year & Week)

KK = Lot Traceability Code

FFSPF0865A = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSPF0865A

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^{\circ}C$, Unless otherwise noted)

Symbol	Parameter		FFSPF0865A	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	650	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	49	mJ	
lF	Continuous Rectified Forward Current @ T _C <	8	Α	
	Continuous Rectified Forward Current @ T _C <	6.8		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	670	Α
		T _C = 150°C, 10 μs	640	Α
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	49	А
I _{F, RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	25	Α
P _{tot}	Power Dissipation	T _C = 25 C	39	W
		T _C = 150°C	6.4	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to + 175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	mbol Parameter		Unit
$R_{ hetaJC}$	Thermal Resistance, Junction to Case, Max.	4.0	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 8 A, T _C = 25°C	-	1.50	1.75	V
		I _F = 8 A, T _C = 125°C	-	1.6	2.0	
		I _F = 8 A, T _C = 175°C	-	1.72	2.4	
I _R	Reverse Current	V _R = 650 V, T _C = 25°C	-	-	200	μΑ
		V _R = 650 V, T _C = 125°C	-	_	400	
		V _R = 650 V, T _C = 175°C	-	_	600	
Q_{C}	Total Capacitive Charge	V = 400 V	-	27	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	463	_	pF
		V _R = 200 V, f = 100 kHz	-	48	_	
		V _R = 400 V, f = 100 kHz	-	38	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. E_{AS} of 49 mJ is based on starting TJ = 25°C, L = 0.5 mH, I_{AS} = 14 A, V = 50 V.

ORDERING INFORMATION

Device	Marking	Package	Packing Method	Quantity
FFSPF0865A	FFSPF0865A	TO-220 FP / TO-220F-2FS	Tube	50 units

FFSPF0865A

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

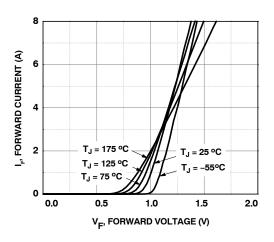


Figure 1. Forward Characteristics

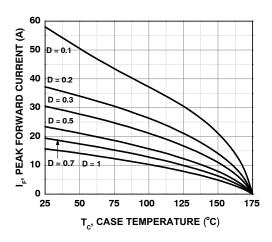


Figure 3. Current Derating

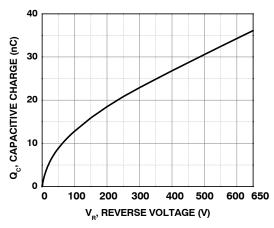


Figure 5. Capacitive Charge vs. Reverse Voltage

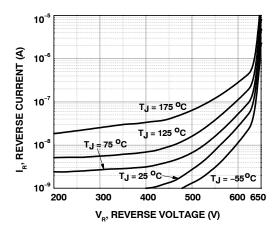


Figure 2. Reverse Characteristics

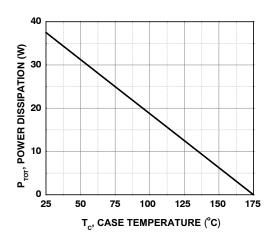


Figure 4. Power Derating

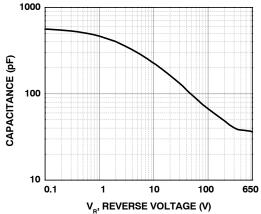


Figure 6. Capacitance vs. Reverse Voltage

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TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

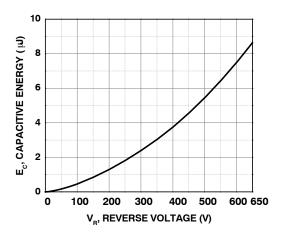


Figure 7. Capacitance Stored Energy

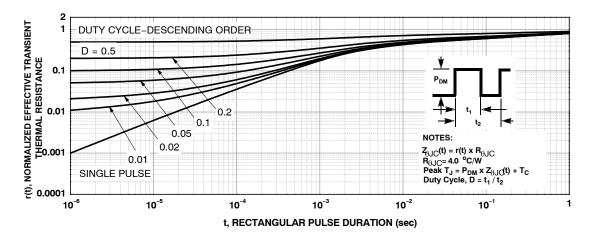


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

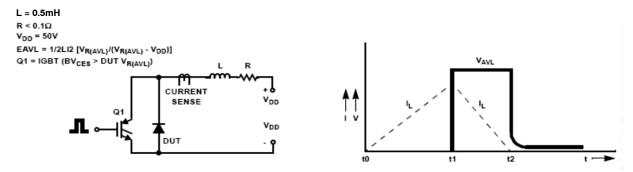
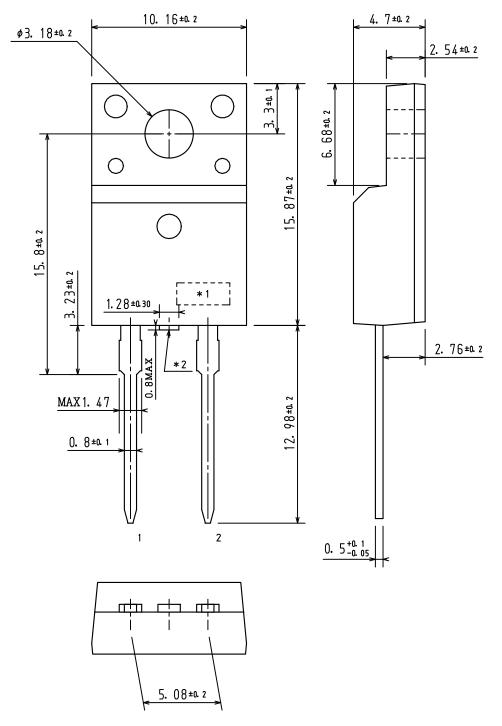
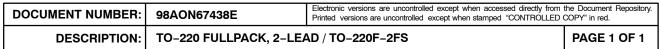


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

TO-220 Fullpack, 2-Lead / TO-220F-2FS CASE 221AS ISSUE O

DATE 29 FEB 2012





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